

SILICON POWER MOS FET NE552R479A

3.0 V OPERATION SILICON RF POWER LDMOS FET FOR 2.45 GHz 0.4 W TRANSMISSION AMPLIFIERS

DESCRIPTION

The NE552R479A is an N-channel silicon power laterally diffused MOS FET specially designed as the transmission power amplifier for 3.0 V WLL products. Dies are manufactured using our NEWMOS2 technology (our WSi gate laterally diffused MOS FET) and housed in a surface mount package. This device can deliver 26.0 dBm output power with 45% power added efficiency at 2.45 GHz under the 3.0 V supply voltage.

FEATURES

- High output power : $P_{out} = 26.0$ dBm TYP. ($V_{DS} = 3.0$ V, $I_{Dset} = 200$ mA, $f = 2.45$ GHz, $P_{in} = 19$ dBm)
- High power added efficiency : $\eta_{add} = 45\%$ TYP. ($V_{DS} = 3.0$ V, $I_{Dset} = 200$ mA, $f = 2.45$ GHz, $P_{in} = 19$ dBm)
- High linear gain : $G_L = 11$ dB TYP. ($V_{DS} = 3.0$ V, $I_{Dset} = 200$ mA, $f = 2.45$ GHz, $P_{in} = 10$ dBm)
- Surface mount package : $5.7 \times 5.7 \times 1.1$ mm MAX.
- ★ • Single supply : $V_{DS} = 2.8$ to 6.0 V

APPLICATIONS

- Digital cellular phones : 3.0 V GSM1900 Pre Driver
- Analog cellular phones : 2.8 V AMPS Handsets
- Bluetooth™ applications : 3.0 V Class 1 Devices
- Others : 3.0 V Two-Way Pagers

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
NE552R479A-T1	79A	AW	• 12 mm wide embossed taping • Gate pin face the perforation side of the tape • Qty 1 kpcs/reel
NE552R479A-T1A			• 12 mm wide embossed taping • Gate pin face the perforation side of the tape • Qty 5 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE552R479A

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V _{DS}	15.0	V
Gate to Source Voltage	V _{GS}	5.0	V
Drain Current	I _D	300	mA
Drain Current (Pulse Test)	I _D ^{Note}	600	mA
Total Power Dissipation	P _{tot}	10	W
Channel Temperature	T _{ch}	125	°C
Storage Temperature	T _{stg}	–55 to +125	°C

Note Duty Cycle 50%, T_{on} ≤ 1 s

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
★ Drain to Source Voltage	V _{DS}		2.8	3.0	6.0	V
Gate to Source Voltage	V _{GS}		0	2.0	3.0	V
Drain Current	I _D	Duty Cycle 50%, T _{on} ≤ 1 s	–	200	500	mA
Input Power	P _{in}	f = 2.45 GHz, V _{DS} = 3.0 V	18	19	25	dBm

ELECTRICAL CHARACTERISTICS

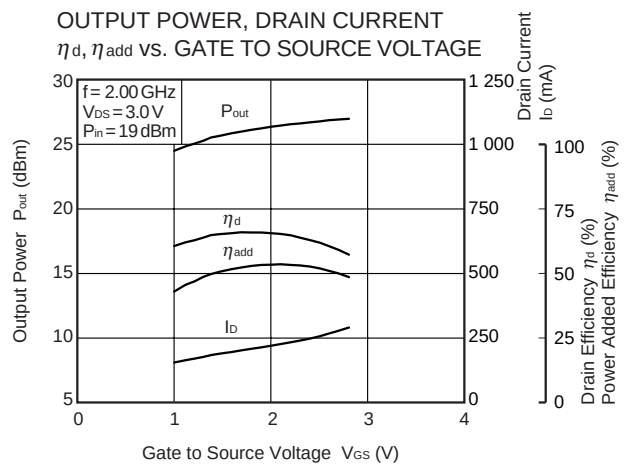
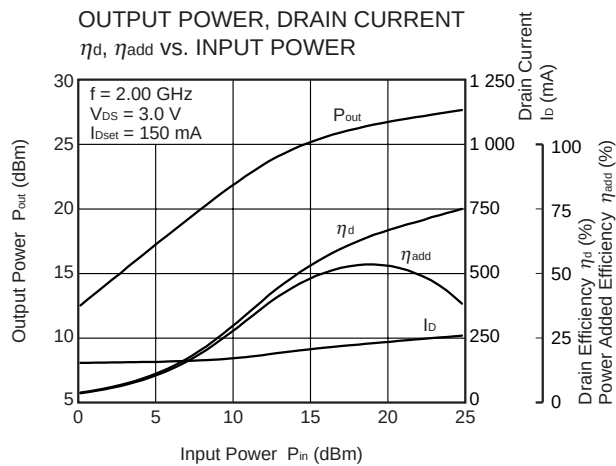
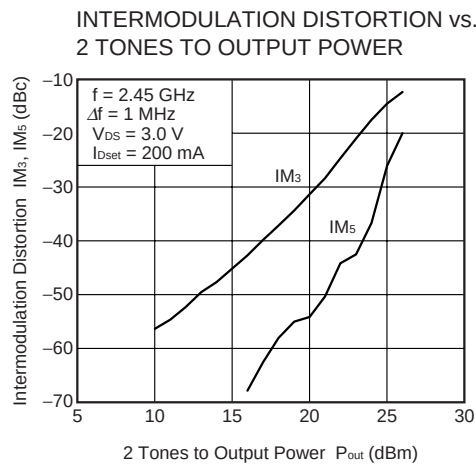
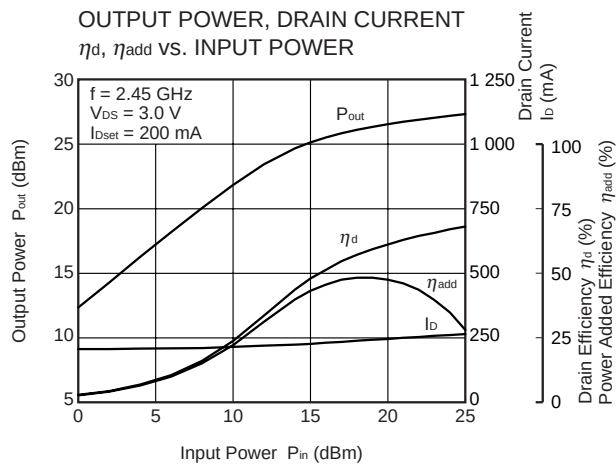
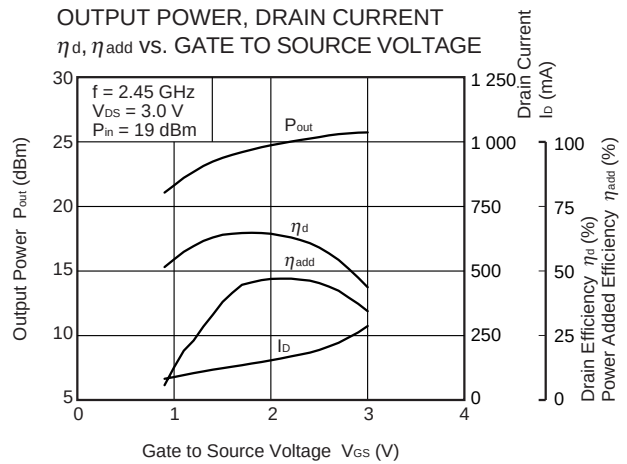
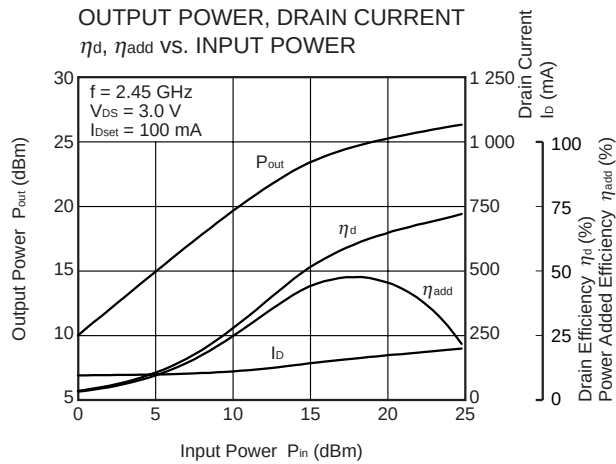
(T_A = +25°C, unless otherwise specified, using NEC standard test fixture)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I _{GSS}	V _{GS} = 5.0 V	–	–	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I _{DSS}	V _{DS} = 6.0 V	–	–	100	nA
Gate Threshold Voltage	V _{th}	V _{DS} = 3.5 V, I _D = 1 mA	1.0	1.4	1.9	V
Thermal Resistance	R _{th}	Channel to Case	–	–	10	°C/W
Transconductance	G _m	V _{DS} = 3.5 V, I _D = 100 mA	–	0.4	–	S
Drain to Source Breakdown Voltage	BV _{DSS}	I _{DSS} = 10 μA	15	18	–	V
Output Power	P _{out}	f = 2.45 GHz, V _{DS} = 3.0 V, P _{in} = 19 dBm, I _{Dset} = 200 mA (RF OFF), Note1	24.0	26.0	–	dBm
Drain Current	I _D		–	230	–	mA
Power Added Efficiency	η _{add}		35	45	–	%
Linear Gain ^{Note2}	G _L		–	11	–	dB

Notes 1. DC performance is 100% testing. RF performance is testing several samples per wafer.
Wafer rejection criteria for standard devices is 1 reject for several samples.

2. P_{in} = 10 dBm

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$)



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

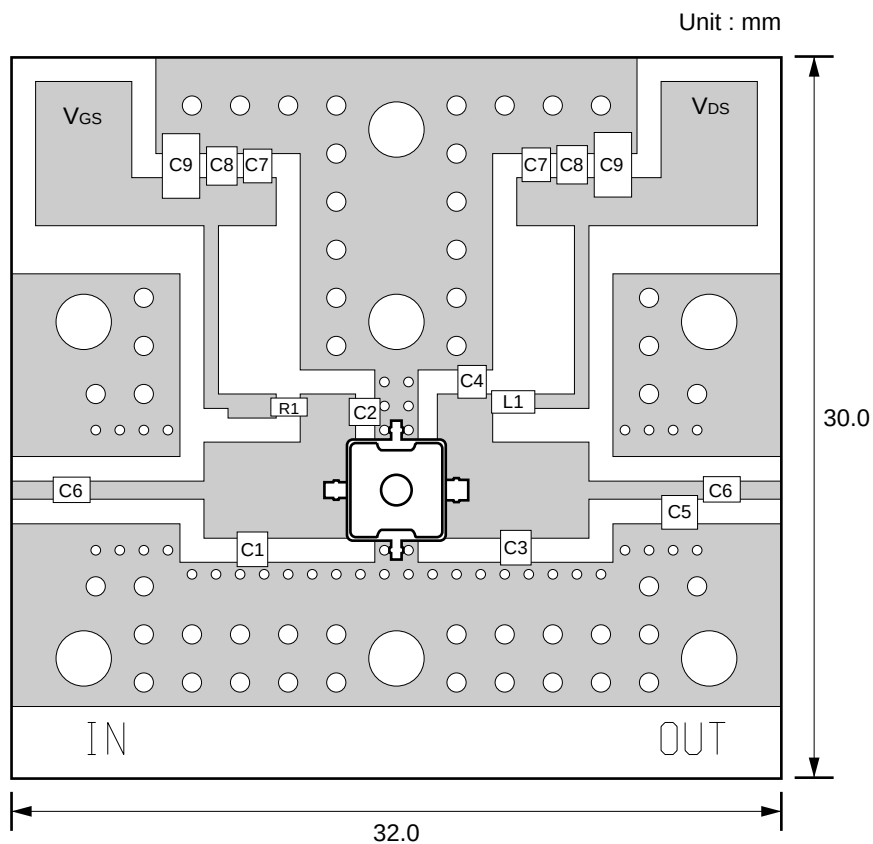
URL <http://www.csd-nec.com/>

LARGE SIGNAL IMPEDANCE ($V_{ds} = 3.0$ V, $I_b = 200$ mA, $f = 2.45$ GHz, $P_{out} = 400$ mW)

f (GHz)	Z_{in} (Ω)	Z_{OL} (Ω) ^{Note}
2.45	2.96 -j7.78	3.36 -j8.42

Note Z_{OL} is the conjugate of optimum load impedance at given voltage, idling current, input power and frequency.

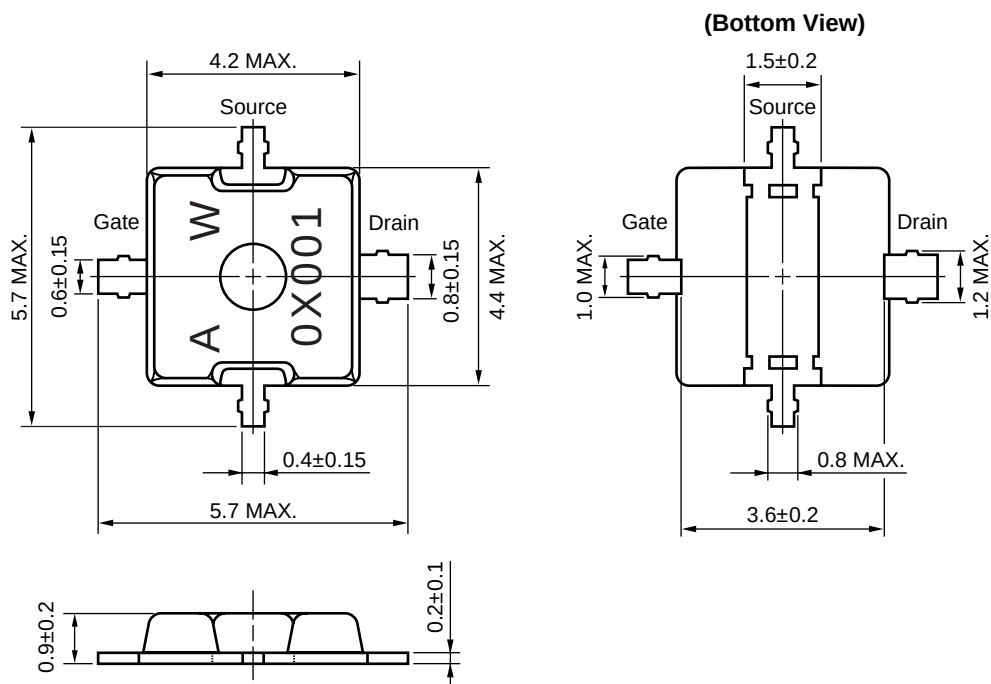
★ EVALUATION BOARD FOR 2.45 GHz



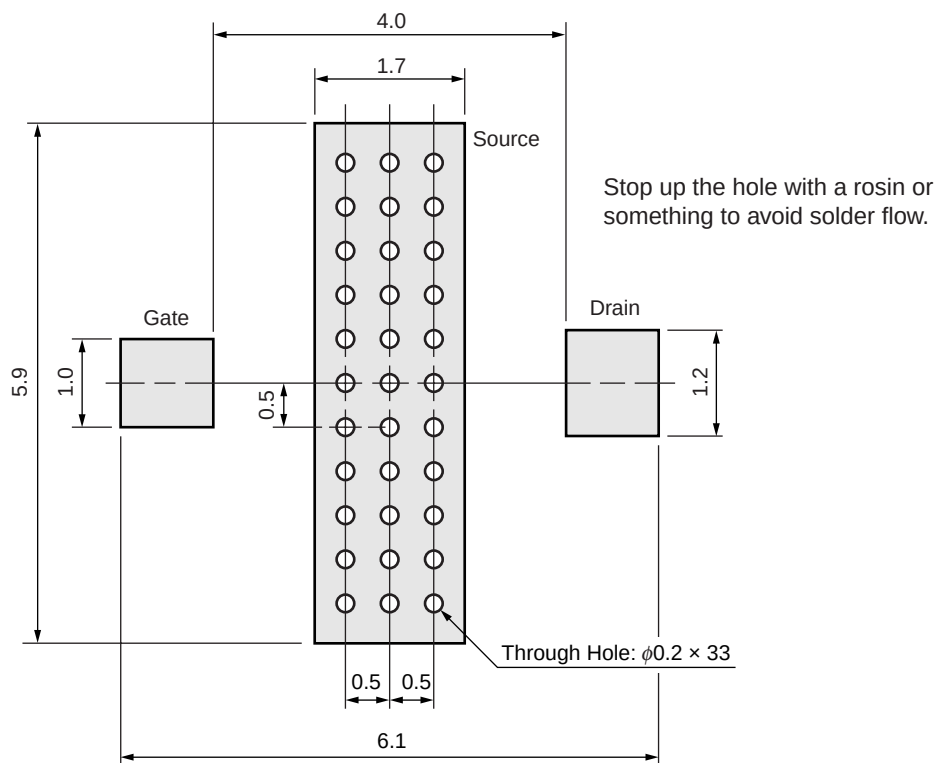
Symbol	Value	Comment
C1	2.0 pF	
C2	1.4 pF	
C3	2.2 pF	
C4	0.8 pF	
C5	0.5 pF	
C6	10 pF	
C7	1 000 pF	
C8	0.22 μ F	
C9	3.3 μ F - 16V	
R1	1 000 Ω	
L1	22 nH	
Circuit Board	t = 0.4 mm, ϵ r = 4.5	R4775

★ PACKAGE DIMENSIONS

79A (UNIT: mm)



79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) : 215°C or below Time at temperature of 200°C or higher : 25 to 40 seconds Preheating time at 120 to 150°C : 30 to 60 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per pin of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).

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► For further information, please contact

NEC Compound Semiconductor Devices, Ltd. <http://www.csd-nec.com/>

E-mail: salesinfo@csd-nec.com (sales and general)

techinfo@csd-nec.com (technical)

5th Sales Group, Sales Division TEL: +81-44-435-1588 FAX: +81-44-435-1579

NEC Compound Semiconductor Devices Hong Kong Limited

E-mail: ncsd-hk@elhk.nec.com.hk (sales, technical and general)

Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309

Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859

Korea Branch Office TEL: +82-2-558-2120 FAX: +82-2-558-5209

NEC Electronics (Europe) GmbH <http://www.ee.nec.de/>

TEL: +49-211-6503-01 FAX: +49-211-6503-487

California Eastern Laboratories, Inc. <http://www.cel.com/>

TEL: +1-408-988-3500 FAX: +1-408-988-0279